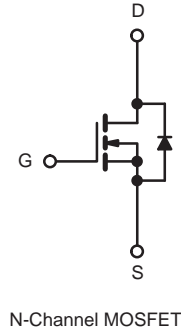


N-Channel 80 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)
80	0.0021 at V _{GS} = 10 V	200	168 nC
	0.0027 at V _{GS} = 4.5 V	180	



FEATURES

- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	80	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	200
		T _C = 125 °C	140
Pulsed Drain Current (t = 100 μs)	I _{DM}	800	A
Avalanche Current	I _{AS}	L = 0.1 mH	190
Single Avalanche Energy ^a			E _{AS}
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	300 ^b
		T _C = 125 °C	125 ^b
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	2.1	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.5	

Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

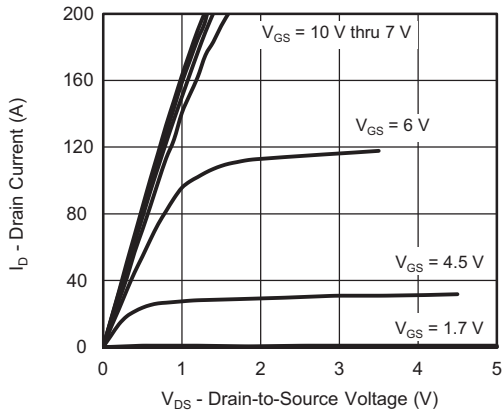
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	100	
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	2	mA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	200	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	-	0.0021	0.0027	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$	-	0.0028	0.0036	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	-	90	-	S
Dynamic ^b						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$	-	10500	-	pF
Output Capacitance	C_{OSS}		-	1650	-	
Reverse Transfer Capacitance	C_{RSS}		-	75	-	
Total Gate Charge ^c	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	-	168	-	nC
Gate-Source Charge ^c	Q_{gs}		-	55	-	
Gate-Drain Charge ^c	Q_{gd}		-	23	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	-	2.3	-	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 1.67\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	28	-	ns
Rise Time ^c	t_r		-	75	-	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	88	-	
Fall Time ^c	t_f		-	32	-	
Drain-Source Body Diode Ratings and Characteristics ^b ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current ($t = 100\text{ }\mu\text{s}$)	I_{SM}		-	-	800	A
Forward Voltage ^a	V_{SD}	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$	-	0.7	1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	118	-	ns
Peak Reverse Recovery Charge	$I_{RM(REC)}$		-	5	10	A
Reverse Recovery Charge	Q_{rr}		-	305	-	μC

Notes

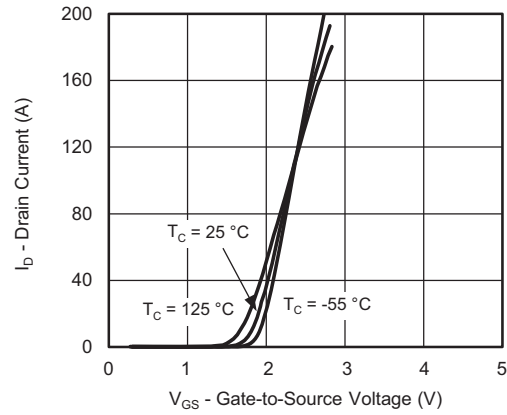
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

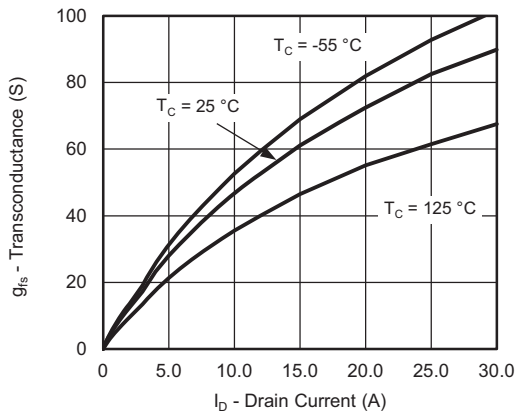
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



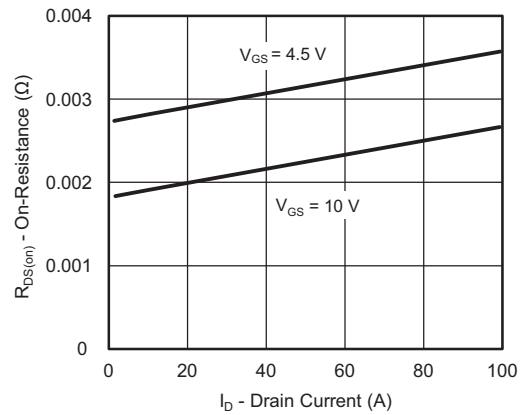
Output Characteristics



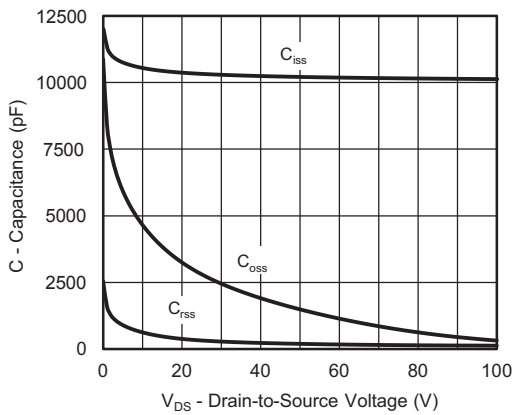
Transfer Characteristics



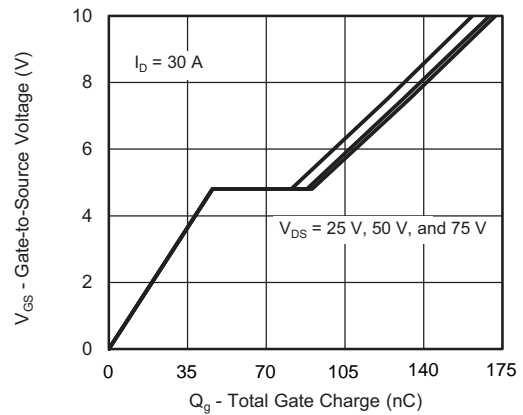
Transconductance



On-Resistance vs. Drain Current

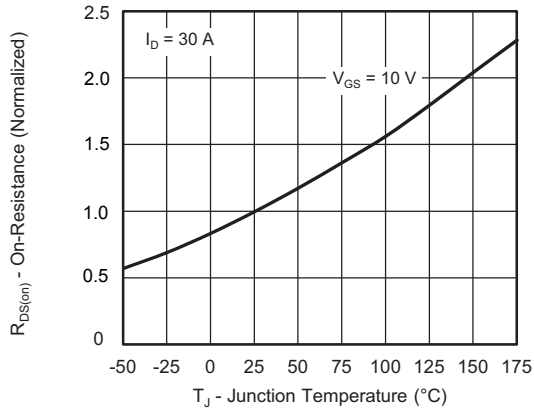


Capacitance

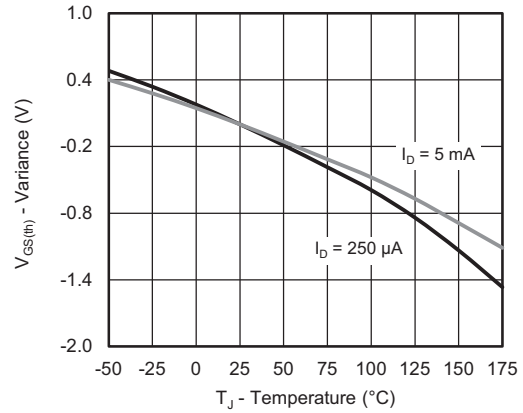


Gate Charge

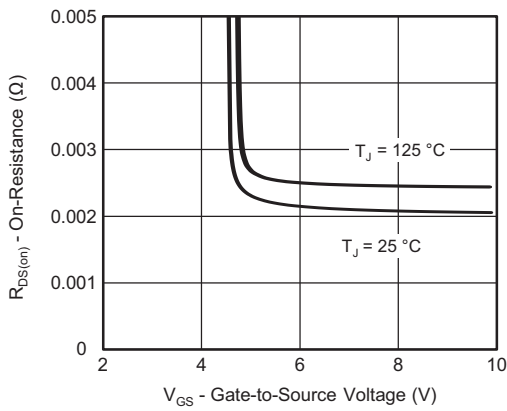
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



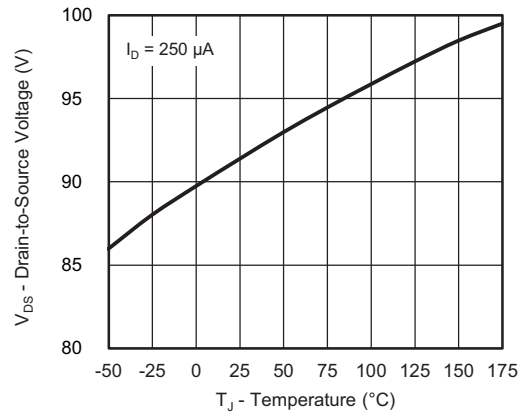
On-Resistance vs. Junction Temperature



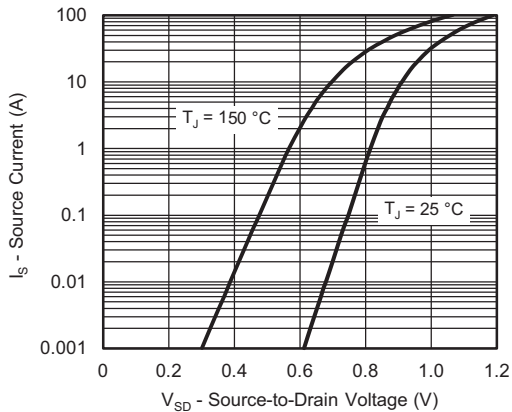
Threshold Voltage



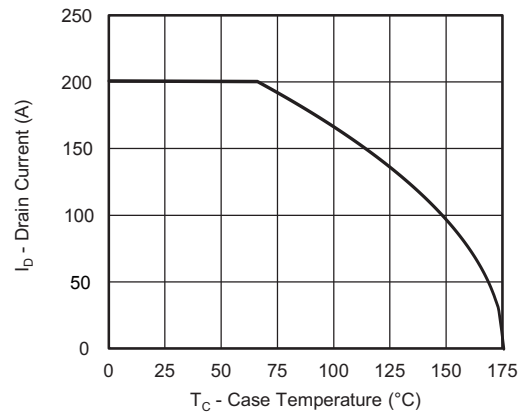
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

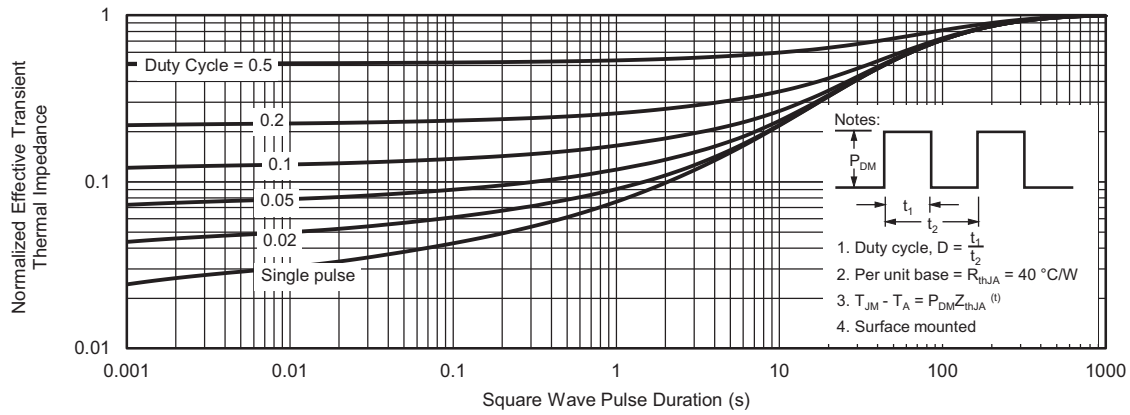
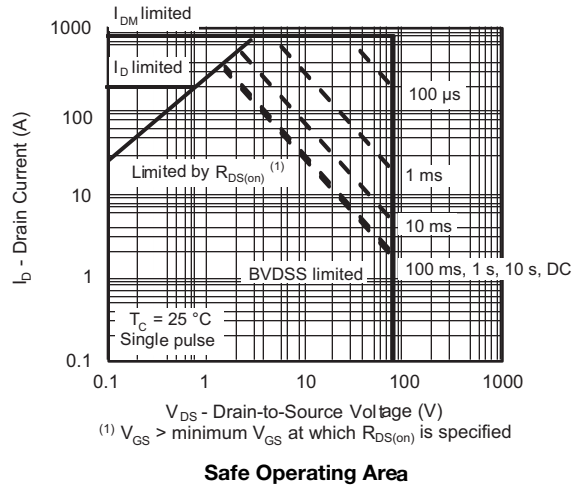


Source Drain Diode Forward Voltage



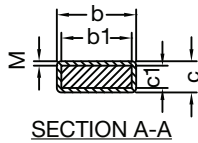
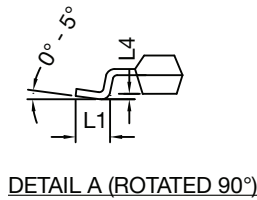
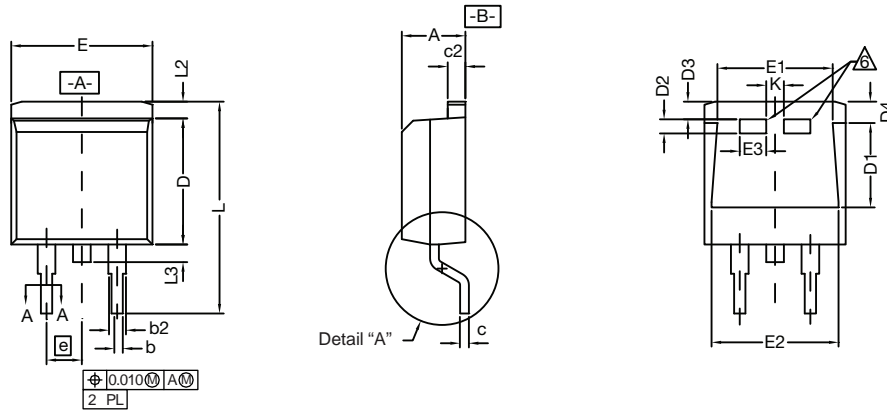
Current De-Rating

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

TO-263 (D²PAK): 3-LEAD

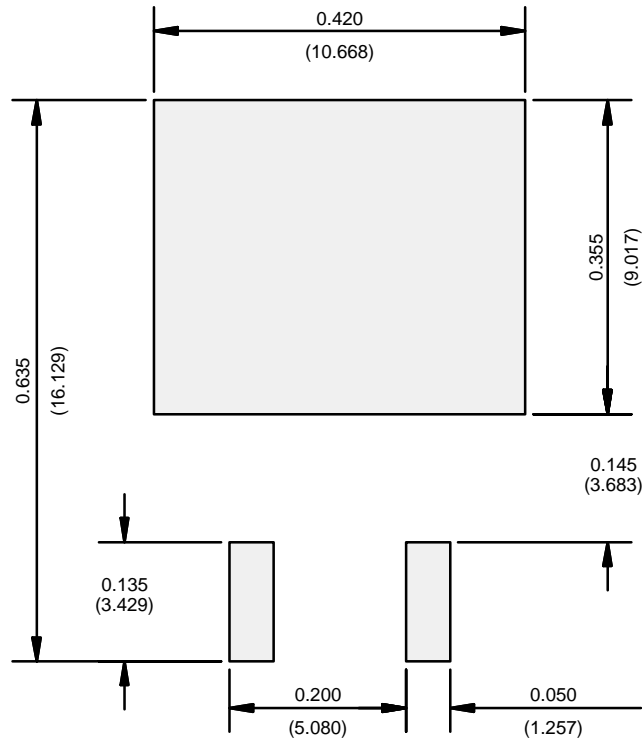


DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.154	0.196	3.908	4.976	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.332	0.388	8.438	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.375	0.417	9.545	10.596	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.559	0.629	14.215	15.985	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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